

33082R003

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : NANBU, et al.

Serial No. : 09/233,073

Filed : January 19, 1999

For : METHOD OF ETCHING



Examiner: Vinh, L.

Group Art Unit: 1765

AMENDMENT

Assistant Commissioner For Patents  
Washington, DC 20231

Sir:

In response to the Office Action of November 15, 1999, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please amend the specification as follows:

Page 5, line 36, change "2" to --22--.

Page 7, line 22, change "satisfactorily" to --satisfactory--.

Page 9, line 35, change "hear" to --near--.

IN THE CLAIMS

Please add new claims 4 to 14, which read as follows:

--4. The etching method according to claim 1, wherein the etching gas supply rate is 8.4 sccm to 16.9 sccm for a substantial volume of one liter of the reaction chamber.

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